

TM30N03BDF

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

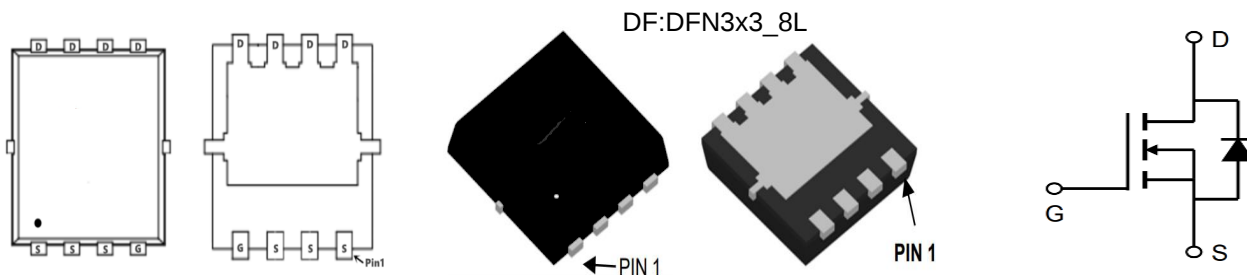
General Features

$V_{DS} = 30V$ $I_D = 30A$

$R_{DS(ON)} = 9m\Omega (typ.) @ V_{GS} = 10V$

100% UIS Tested

100% R_g Tested



Marking: 30N03

Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
I_{DM}	Pulsed Drain Current ²	90	A
EAS	Single Pulse Avalanche Energy ³	19	mJ
I_{AS}	Avalanche Current	25	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	10	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	85	$^\circ C/W$

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Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	9	14	mΩ
		V _{GS} =4.5V, I _D =5A	-	15	22.5	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	633	-	pF
C _{oss}	Output Capacitance		-	120	-	pF
C _{rss}	Reverse Transfer Capacitance		-	99	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =10A, V _{GS} =10V	-	15	-	nC
Q _{gs}	Gate-Source Charge		-	4.7	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V,I _D =18A, R _{GEN} =3Ω, V _{GS} =10V	-	5	-	ns
t _r	Turn-on Rise Time		-	8	-	ns
t _{d(off)}	Turn-off Delay Time		-	21	-	ns
t _f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	30	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	72	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =18A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =18A,dI/dt=100A/μs	-	7	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	5.9	-	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=20A$
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Figure 1: Output Characteristics

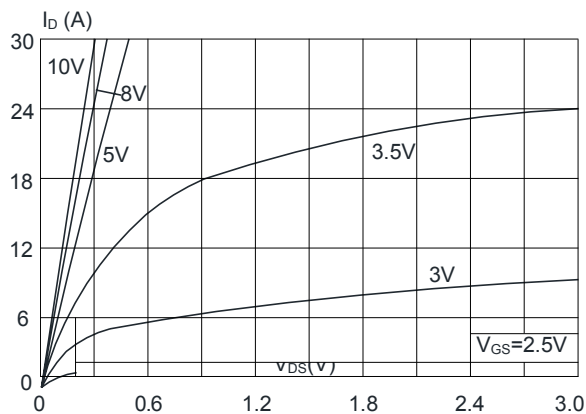


Figure 2: Typical Transfer Characteristics

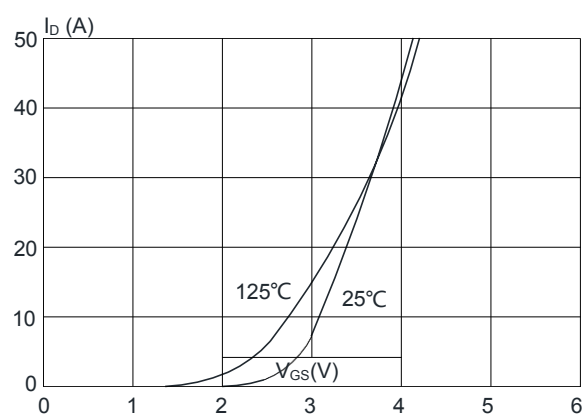


Figure 3: On-resistance vs. Drain Current

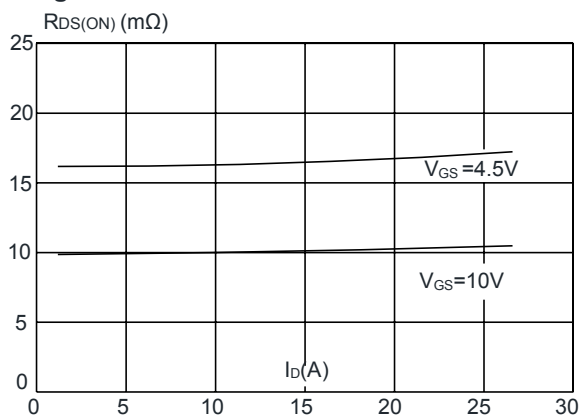


Figure 4: Body Diode Characteristics

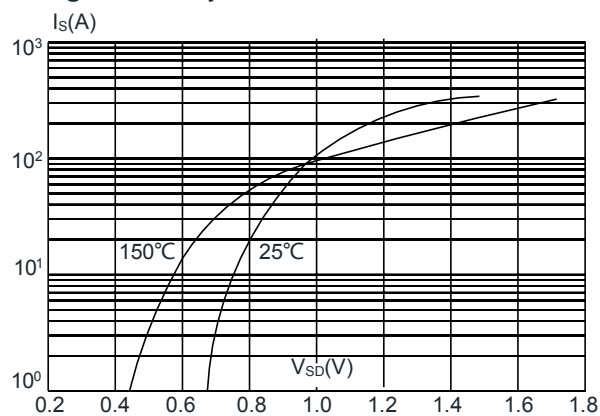


Figure 5: Gate Charge Characteristics

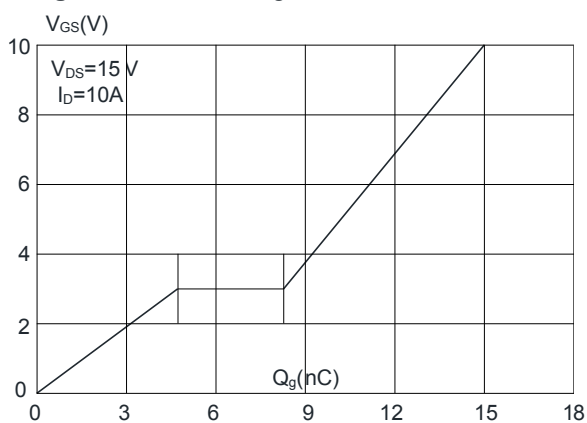
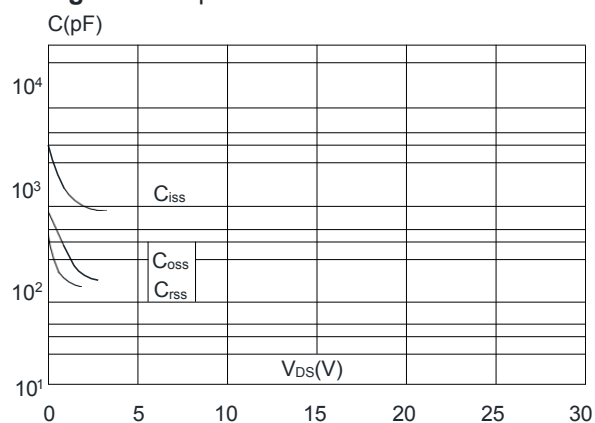


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

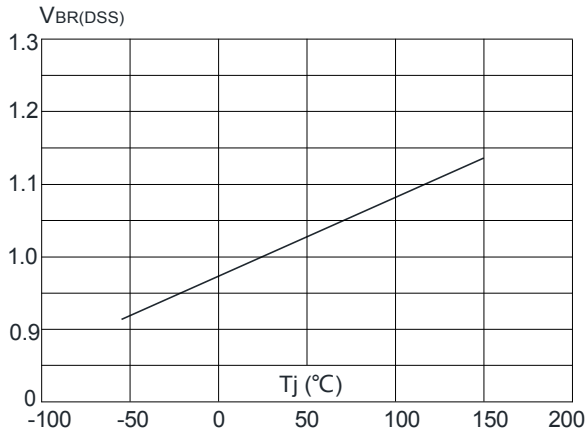


Figure 8: Normalized on Resistance vs. Junction Temperature

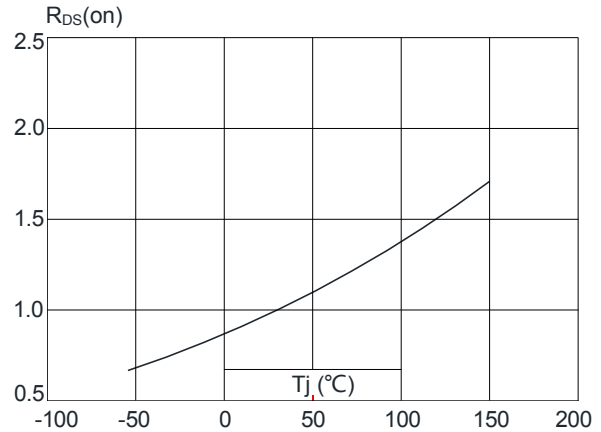


Figure 9: Maximum Safe Operating Area

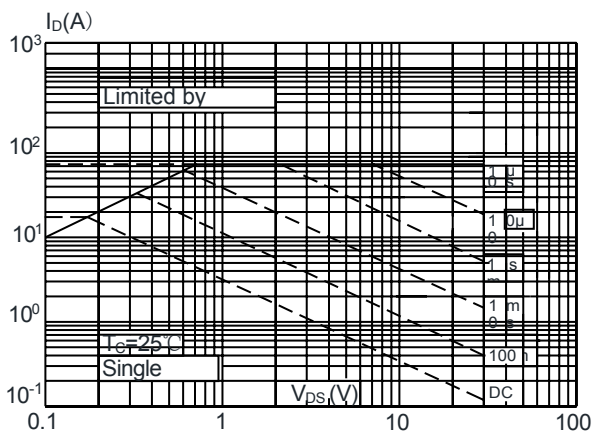


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

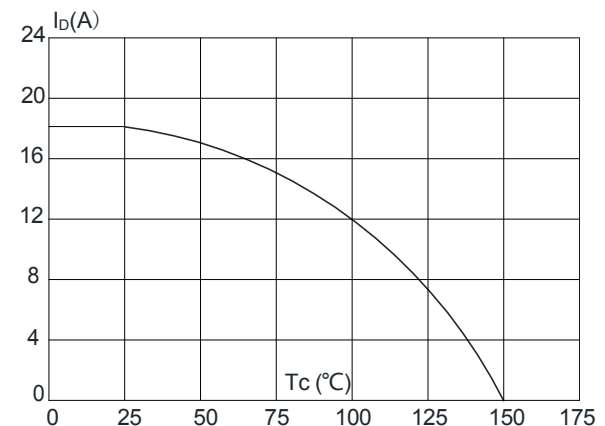
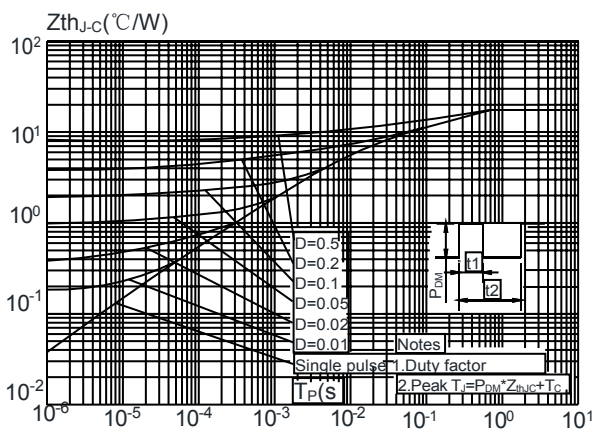


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

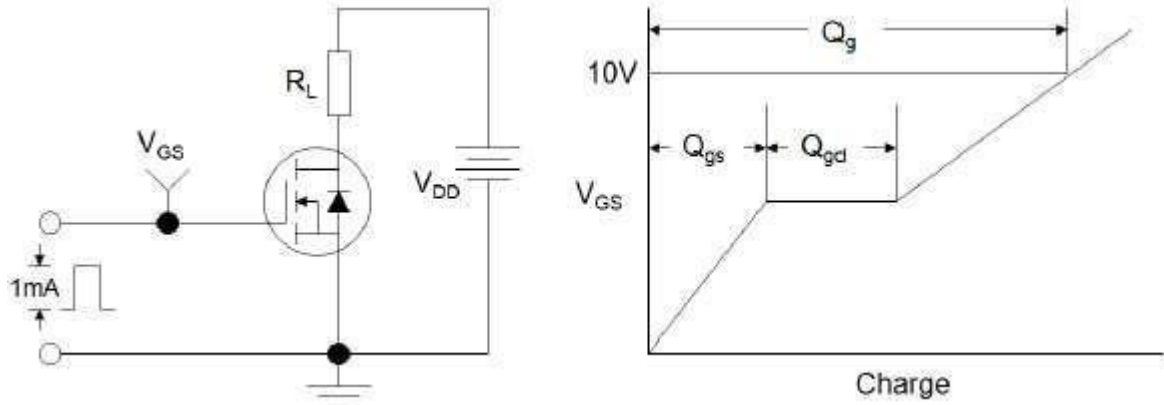


Figure1: Gate Charge Test Circuit & Waveform

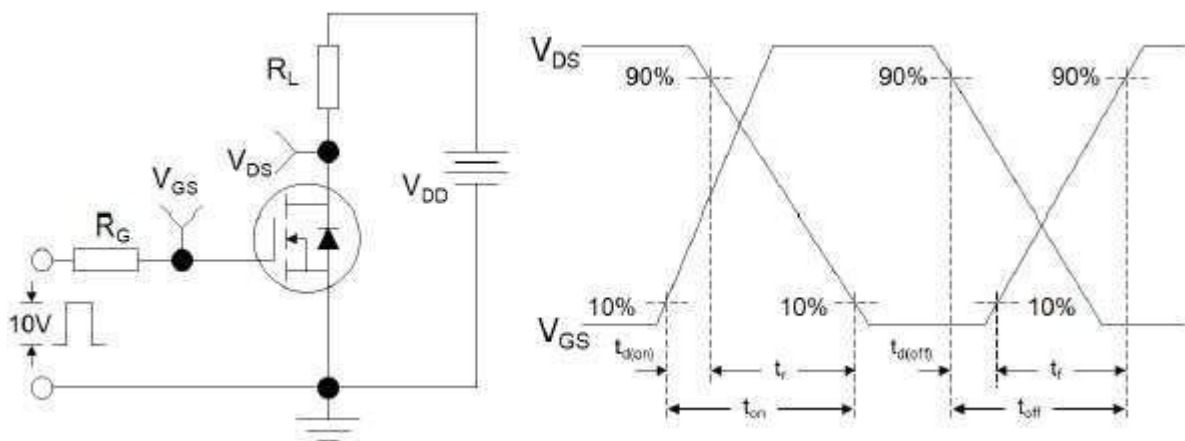


Figure 2: Resistive Switching Test Circuit & Waveforms

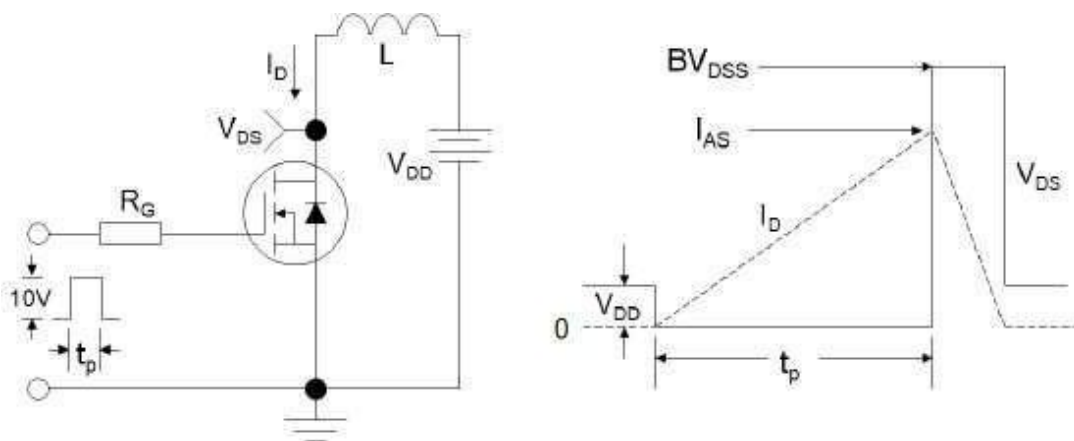
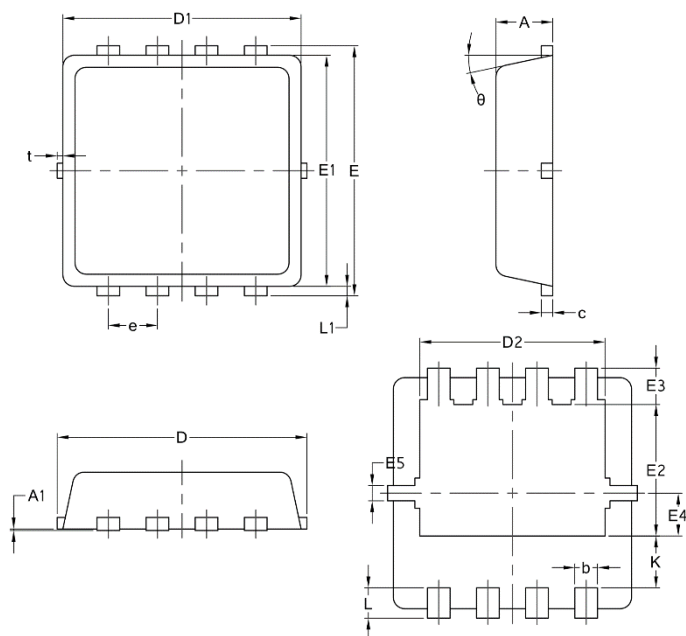


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data:DFN3x3-8L



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14